

Final Exam, ECE 137A

Thursday March 20, 2025, Noon- 3 p.m.

Name: _____

Closed Book Exam:

Class Crib-Sheet and 2 pages (4 surfaces) of student notes permitted

Do not open this exam until instructed to do so. Use any and all reasonable approximations (5% accuracy), *after stating & justifying them.*

Show your work:

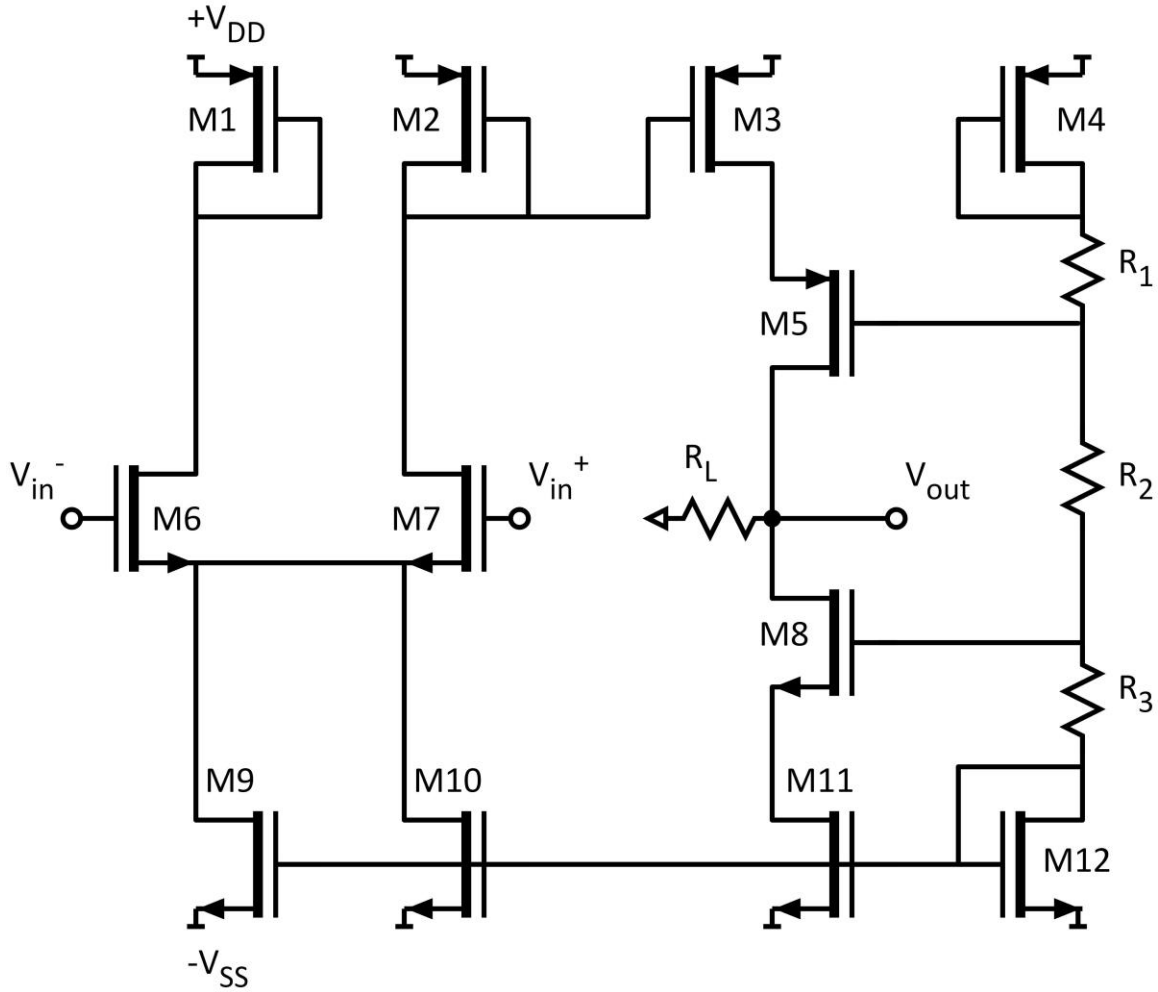
Full credit will not be given for correct answers if supporting work is missing.

Good luck

Part	Points Received	Points Possible	Part	Points Received	Points Possible
1a		5	2b		5
1b		5	2c		15
1c		5	2d		10
1d		12	3a		5
1e		8	3b		10
1f		10	3c		5
2a		5			
total		100			

Problem 1, 45 points

This is an NOT an Op-Amp: Analyze under the assumption that the differential and common mode input voltages are at zero volts.



The NMOSFETs have $K_{\mu} = 10 \text{ mA/V}^2 \cdot (W_g / 1 \mu\text{m})$, $K_v = 2.0 \text{ mA/V} \cdot (W_g / 1 \mu\text{m})$, $\Delta V = 0.10 \text{ V}$, $V_{th} = 0.2 \text{ V}$, $1/\lambda = 5 \text{ V}$. The PMOS have identical parameters, except, of course, V_{th} is negative. $V_{DD} = +0.8 \text{ V}$, $-V_{SS} = -0.8 \text{ V}$

All transistors have $|V_{gs}| = 0.3 \text{ V}$.

M1,2,6,7,9,10 are biased at $I_D = 20 \mu\text{A}$.

M3,5,8,11,4,12 are biased at $I_D = 100 \mu\text{A}$.

The IR voltage drops across R_1 and R_3 are each 200 mV .

$R_L = 10 \text{ k}\Omega$.

Part a, 5 points

DC bias

Find the following:

Gate width of M2 = _____

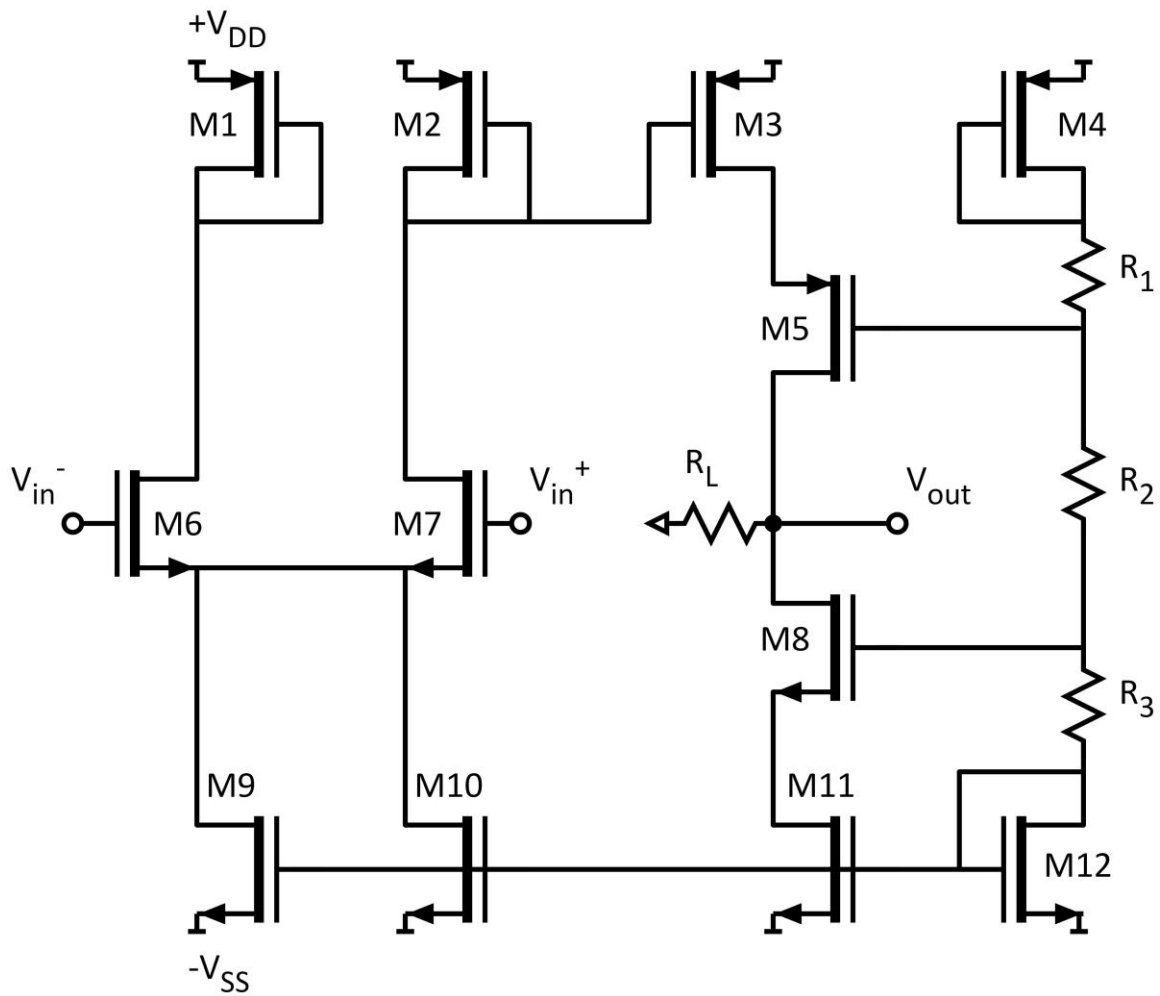
Gate width of M3 = _____

Value of R_1 = _____

Value of R_2 = _____

Part b, 5 points

DC bias



On the circuit diagram above, label the DC voltages at **ALL** nodes.

Part c, 5 points

Find the following

MOSFET M6	$g_m =$ _____	$R_{DS} =$ _____
MOSFET M7	$g_m =$ _____	$R_{DS} =$ _____
MOSFET M2	$g_m =$ _____	$R_{DS} =$ _____
MOSFET M3	$g_m =$ _____	$R_{DS} =$ _____
MOSFET M5	$g_m =$ _____	$R_{DS} =$ _____
MOSFET M8	$g_m =$ _____	$R_{DS} =$ _____
MOSFET M11	$g_m =$ _____	$R_{DS} =$ _____

Part d, 12 points.

Find the following

	Voltage Gain	Input impedance
Transistor combination M3,5,8,11		

Note: You can analyze M3 and M5 as separate stages, or as a combined stage using Norton/Thevenin methods. Don't ask for hints as to how to do this.

Part e, 8 points.

Find the following

	Voltage Gain	Input impedance
Transistor combination M1,2,6,7,9,10		
Overall op-amp $V_{out} / (V_{in}^+ - V_{in}^-)$		

Hint: although M2 is a diode-connected FET, the small-signal resistance of this 2-terminal element, although mostly determined by the FET transconductance, also has a slightly contribution from the FET R_{DS} .

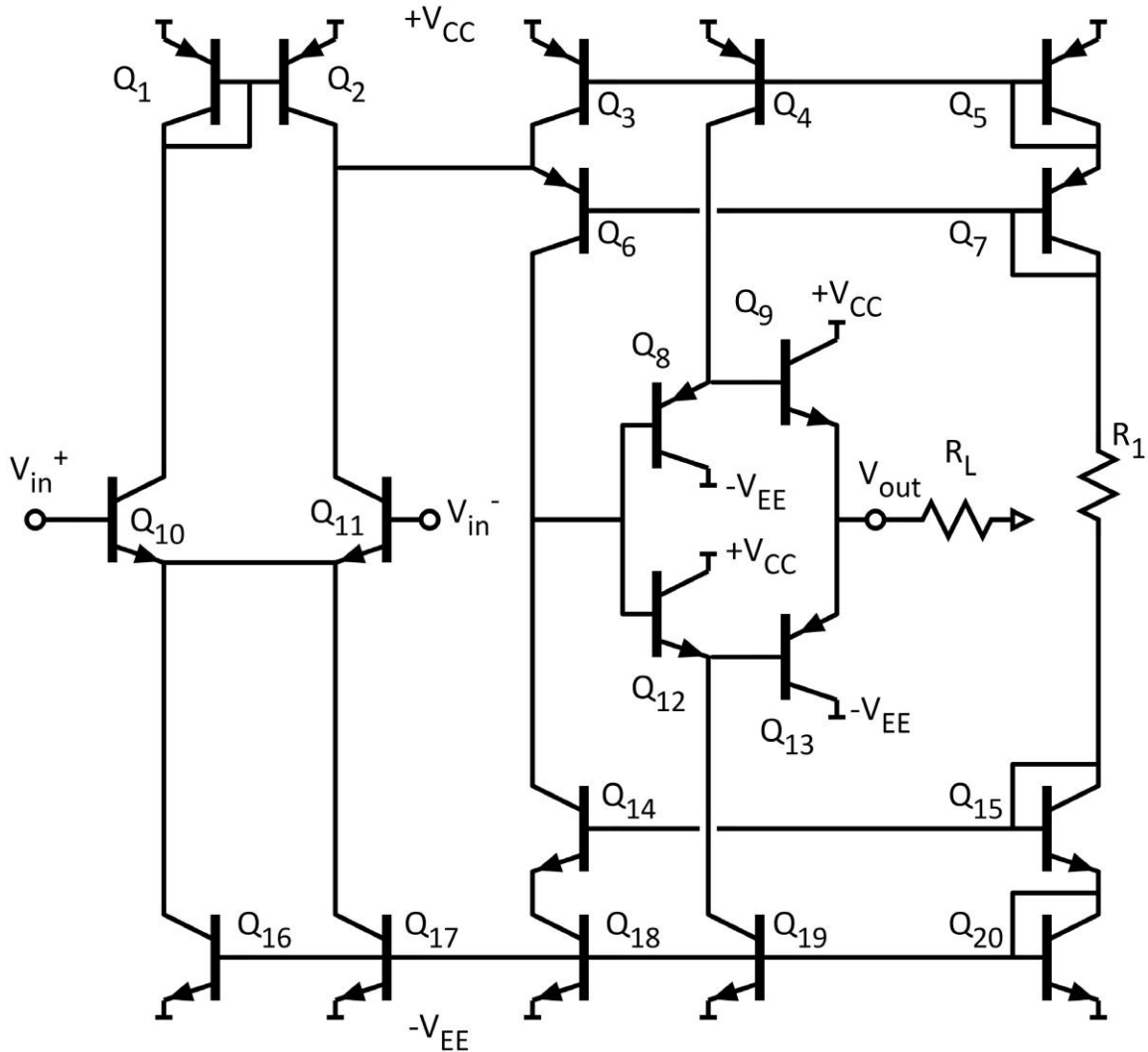
Part f, 10 points

Maximum output voltage swings (*show all your work*).

	magnitude and sign of maximum output signal swing due to <i>cutoff</i>	magnitude and sign of maximum output signal swing due to <i>knee voltage</i>
Transistor M6		Do not calculate
Transistor M7		Do not calculate
Transistor M3		Do not calculate
Transistor M5	Do not calculate	
Transistor M8	Do not calculate	

Problem 2, 35 points

This is an Op-Amp---analyze the bias under the assumption that DC output voltage V_{out} is zero volts, that the positive input V_{in+} is zero volts, and that we must determine the DC value of the negative input voltage (V_{in-}) necessary to obtain this.



All the transistors have the same (matched) I_S , have $\beta = \infty$, and $V_A = 100$ Volts.

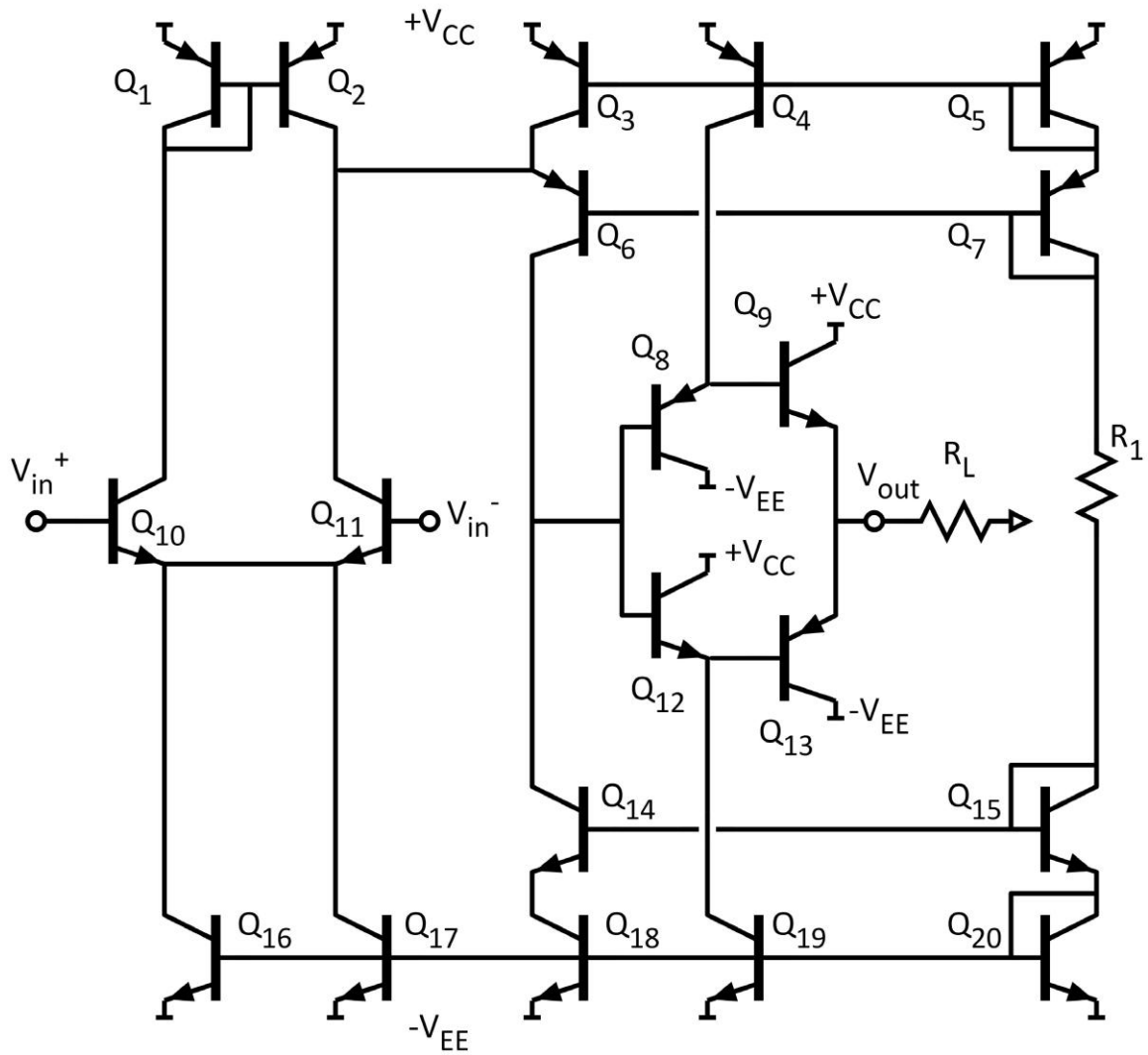
$V_{CE(sat)} = 0.5V$. V_{be} is approximately $0.7V$, but use the exact relationship

$V_{be} = (kT/q) \ln(I_E / I_S)$ when appropriate. The supplies are $+5$ Volts and -5 Volts. All transistors have the same I_S , and all are biased at 0.1 mA collector current.

$R_L = 1$ kOhm.

Part a, 5 points

DC bias



On the circuit diagram above, label the DC voltages at **ALL nodes**.

Part b, 5 points.

Find the following

	Voltage Gain	Input impedance
Transistor combination Q8,9,12,13		

Part c, 15 points.

Find the following

	Voltage Gain	Input impedance
Transistor combination Q1,2,10,11,6		
Overall op-amp $V_{out} / (V_{in}^+ - V_{in}^-)$		

Note: You can analyze (Q1,2,10,11) and Q6 as separate stages, or as a combined stage using Norton/Thevenin methods. Don't ask for hints as to how to do this.

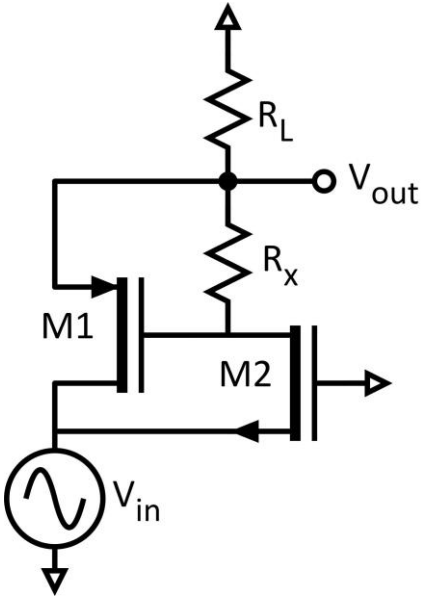
Part d, 10 points

Maximum output voltage swings (*show all your work*).

	magnitude and sign of maximum output signal swing due to <i>saturation voltage</i> (saturation)
Transistor Q4	
Transistor Q9	

Note that transistors Q13 and Q19, Because of the circuit symmetry, Will give similar answers but with a change in sign.

Problem 3, 20 points

 The circuit diagram shows a differential pair of MOSFETs, M1 and M2. The gates of both transistors are connected to a common-mode feedback network consisting of a resistor R_x and a load resistor R_L connected to ground. The source of M1 is connected to the source of M2, which is connected to ground. The output voltage V_{out} is taken from the drain of M1. An input voltage V_{in} is applied to the gate of M1.	You will be working on the circuit to the left Ignore DC bias analysis. You don't need it. M_1 and M_2 have transconductances g_{m1} and g_{m2}. Both transistors have infinite R_{DS}, ...so you don't need to include these elements in the circuit diagram !
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Part a, 5 points

Draw a small-signal equivalent circuit of the circuit.

Part b, 10 points

Derive an algebraic expression for V_{out}/V_{in} in terms of g_{m1} , g_{m2} , R_L , and R_X

$$V_{out}/V_{in} =$$

Part c, 5 points

Set $g_{m1}=1\text{ mS}$, $g_{m2}=2\text{ mS}$, $R_L=3\text{ k}\Omega$, and $R_x=5\text{ k}\Omega$.

Find the numerical value of V_{out}/V_{in}

$$V_{out}/V_{in} =$$

